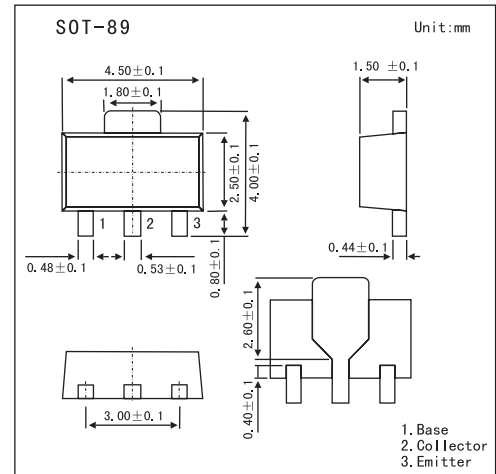


## Epitaxial Planar NPN Transistor

## KTC4373

## ■ Features

- High Voltage:  $V_{CE0}=120V$
- High Transition Frequency:  $f_T=120MHz$
- Small Flat Package

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	120	V
Collector-Emitter Voltage	$V_{CE0}$	120	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Collector Current	$I_C$	800	mA
Base Current	$I_B$	160	mA
Collector Power Dissipation	$P_C$	500	mW
	$P_{C^*}$	1	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 to 150	$^\circ C$

\* mounted on ceramic substrate (250mm<sup>2</sup>X0.8t)

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=120V, I_E=0$			100	nA
Emitter-Cut-off Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_C=10mA, I_B=0$	120			V
Collector-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5			V
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=100mA$	80		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			1.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=5V, I_C=500mA$			1.0	V
Transition Frequency	$f_T$	$V_{CE}=5V, I_C=100mA$		120		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$			30	pF

## ■ hFE Classification

Marking	CO	CY
Rank	O	Y
Type	80~160	120~240